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1 Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

1.1 Revision C

Revision C was published in March 2018. The following is a summary of the changes in revision C of this document.

- The new Microsemi template and format was applied.
- The package outline drawing was updated. For more information, see [Package Outline Drawing](#).

1.2 Revision B

Revision B was published in May 2011. The following is a summary of the changes in revision B of this document.

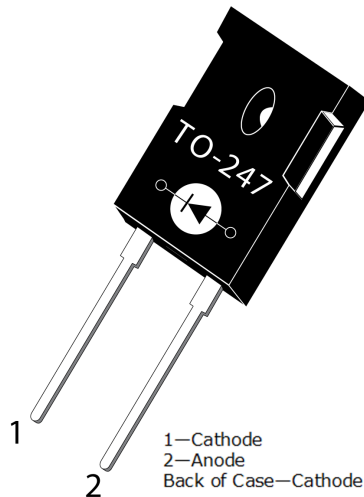
- The patent information was removed from the document.
- For TO-247 packages: the maximum lead thickness was changed from 0.70 in (0.031 mm) to 1.016 in (0.040 mm).

1.3 Revision A

Revision A was published in January 2006. It is the first publication of this document.

2 Product Overview

This section outlines the product overview for the APT60DQ120BG device.



2.1 Features

The following are key features of the APT60DQ120BG device:

- Ultrafast recovery times
- Soft recovery characteristics
- Low forward voltage
- Low leakage current
- Avalanche energy rated
- RoHS compliant
- AEC-Q101 qualified

2.2 Benefits

The following are benefits of the APT60DQ120BG device:

- Higher switching frequency
- Low switching losses
- Low noise (EMI) switching
- Higher reliability systems
- Increased system power density

2.3 Applications

The APT60DQ120BG device is designed for the following applications:

- Power factor correction (PFC)
- Anti-parallel diode
 - Switch-mode power supply
 - Inverters/converters
 - Motor controllers
- Freewheeling diode
 - Switch-mode power supply
 - Inverters/converters
- Snubber/clamp diode

3 Electrical Specifications

This section shows the electrical specifications for the APT60DQ120BG device.

3.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings for the APT60DQ120BG device.

All ratings: $T_c = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_R	Maximum DC reverse voltage	1200	V
V_{RRM}	Maximum peak repetitive reverse voltage	1200	
V_{RWM}	Maximum working peak reverse voltage	1200	
$I_{F(AV)}$	Maximum average forward current ($T_c = 103\text{ }^{\circ}\text{C}$, duty cycle = 0.5)	60	A
$I_{F(RMS)}$	RMS forward current	87	
I_{FSM}	Non-repetitive forward surge current ($T_j = 45\text{ }^{\circ}\text{C}$, 8.3 ms)	540	
E_{AVL}	Avalanche energy (1 A, 40 mH)	20	mJ
T_j, T_{STG}	Operating and storage temperature range	-55 to 175	$^{\circ}\text{C}$
T_L	Lead temperature for 10 seconds	300	

The following table shows the thermal and mechanical characteristics of the APT60DQ120BG device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance			0.40	$^{\circ}\text{C}/\text{W}$
W_t	Package weight		0.22		oz
			5.9		g
Torque	Maximum mounting torque			10	lb-in
				1.1	N-m

3.2 Electrical Performance

The following table shows the static characteristics of the APT60DQ120BG device.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Forward voltage	$I_F = 60\text{ A}$		2.8	3.3	V
		$I_F = 120\text{ A}$		3.35		
		$I_F = 60\text{ A}, T_j = 125\text{ }^{\circ}\text{C}$		2.11		
I_{RM}	Maximum reverse leakage current	$V_R = 1200\text{ V}$			100	μA
		$V_R = 1200\text{ V}, T_j = 125\text{ }^{\circ}\text{C}$			500	
C_j	Junction capacitance	$V_R = 200\text{ V}$		37		pF

3.3 Dynamic Characteristics

The following table shows the dynamic characteristics of the APT60DQ120BG device.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	$I_F = 1\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$ $T_J = 25\text{ }^\circ\text{C}$		30		ns
t_{rr}	Reverse recovery time	$I_F = 60\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		320		
Q_{rr}	Reverse recovery charge	$V_R = 800\text{ V}$ $T_C = 25\text{ }^\circ\text{C}$		630		nC
I_{RRM}	Maximum reverse recovery current			5		A
t_{rr}	Reverse recovery time	$I_F = 60\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$		420		ns
Q_{rr}	Reverse recovery charge	$V_R = 800\text{ V}$		2810		nC
I_{RRM}	Maximum reverse recovery current	$T_C = 125\text{ }^\circ\text{C}$		12		A
t_{rr}	Reverse recovery time	$I_F = 60\text{ A}$ $di_F/dt = -1000\text{ A}/\mu\text{s}$		190		ns
Q_{rr}	Reverse recovery charge	$V_R = 800\text{ V}$ $T_C = 125\text{ }^\circ\text{C}$		4415		nC
I_{RRM}	Maximum reverse recovery current			38		A

3.4 Typical Performance Curves

This section shows the typical performance curves for the APT60DQ120BG device.

Figure 1 • Maximum Transient Thermal Impedance

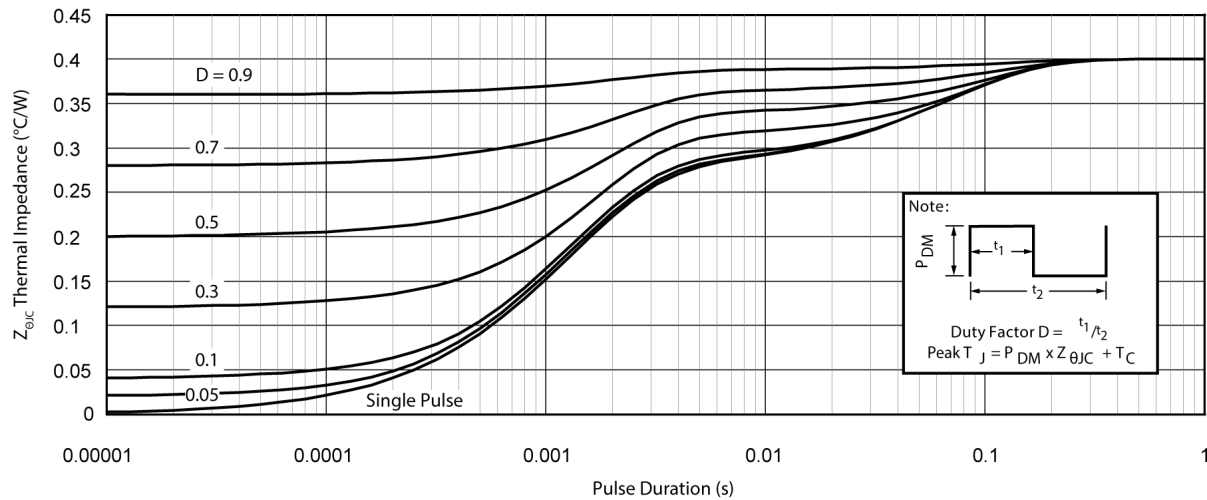


Figure 2 • Forward Current vs. Forward Voltage

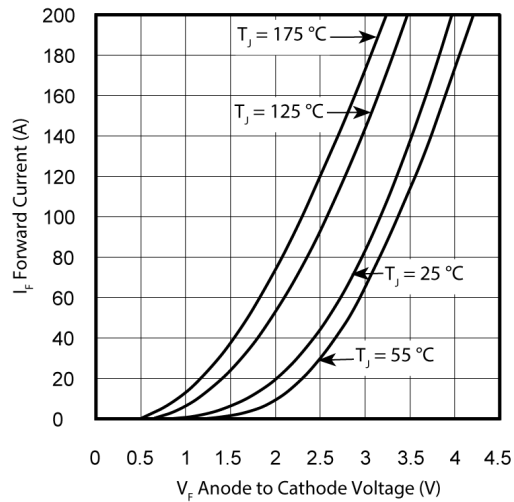


Figure 3 • t_{rr} vs. Current Rate of Change

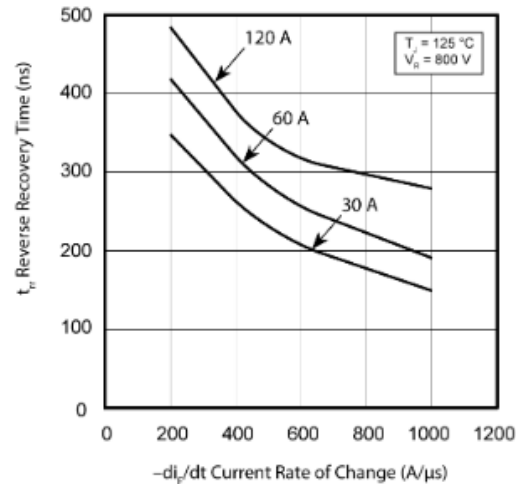
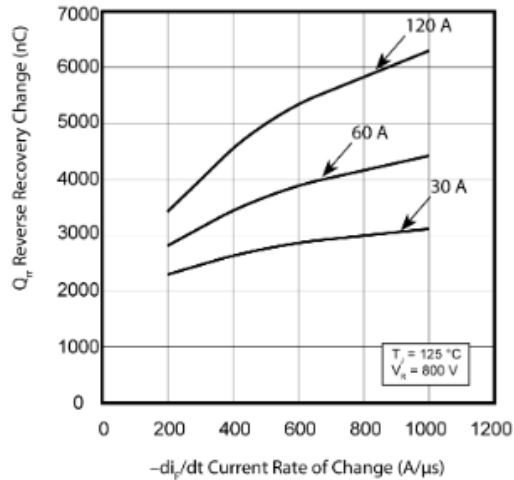
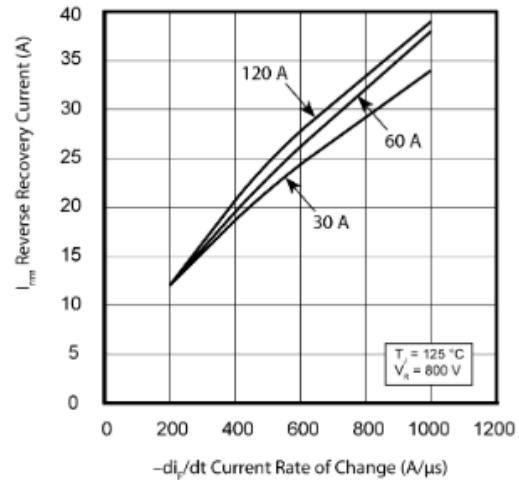
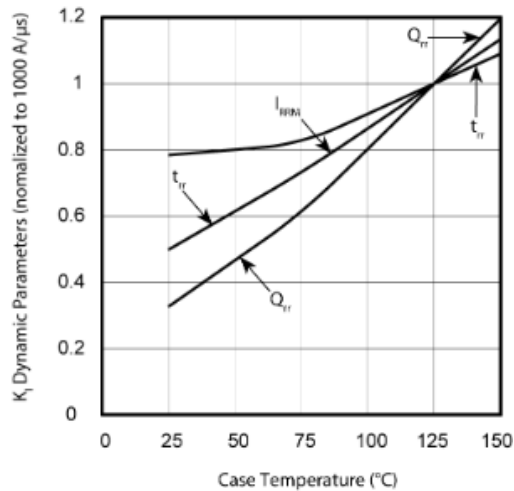
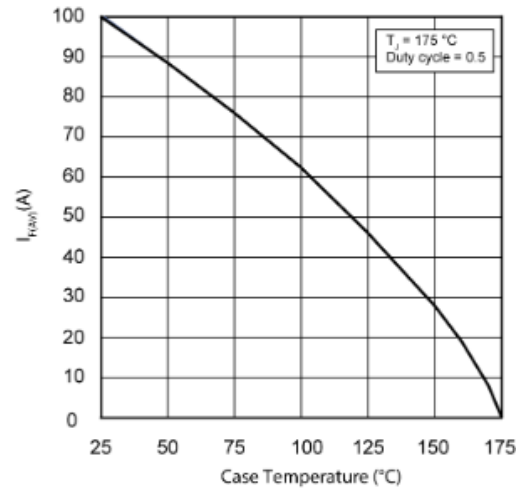
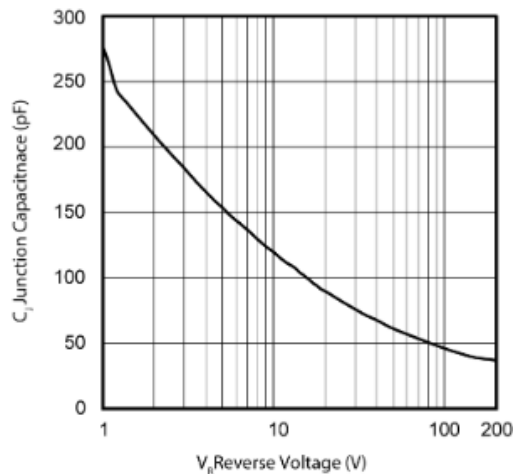
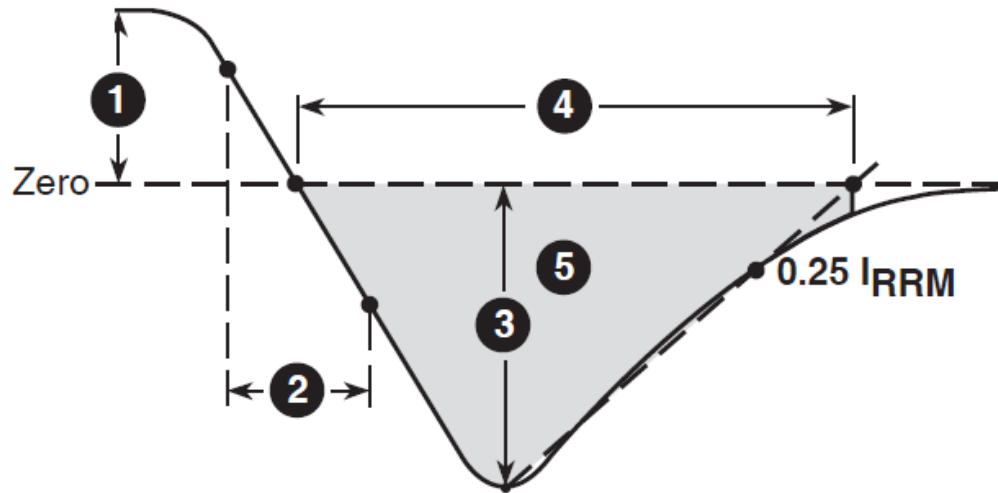


Figure 4 • Q_{rr} vs. Current Rate of Change**Figure 5 • IRRM vs. Current Rate of Change****Figure 6 • Dynamic Parameters vs. Junction Temperature****Figure 7 • Maximum Average Forward Current vs. Case Temperature****Figure 8 • Junction Capacitance vs. Reverse Voltage**

4 Reverse Recovery Overview

The following illustration shows the reverse recovery testing and measurement information for the APT60DQ120BG device.

Figure 9 • Diode Reverse Recovery Waveform and Definitions



1. I_F —Forward conduction current.
2. di_F/dt —Rate of diode current change through zero crossing.
3. I_{RRM} —Maximum reverse recovery current.
4. t_{rr} —Reverse recovery time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \times I_{RRM}$ passes through zero.
5. Q_{rr} —Area under the curve defined by I_{RRM} and t_{rr} .

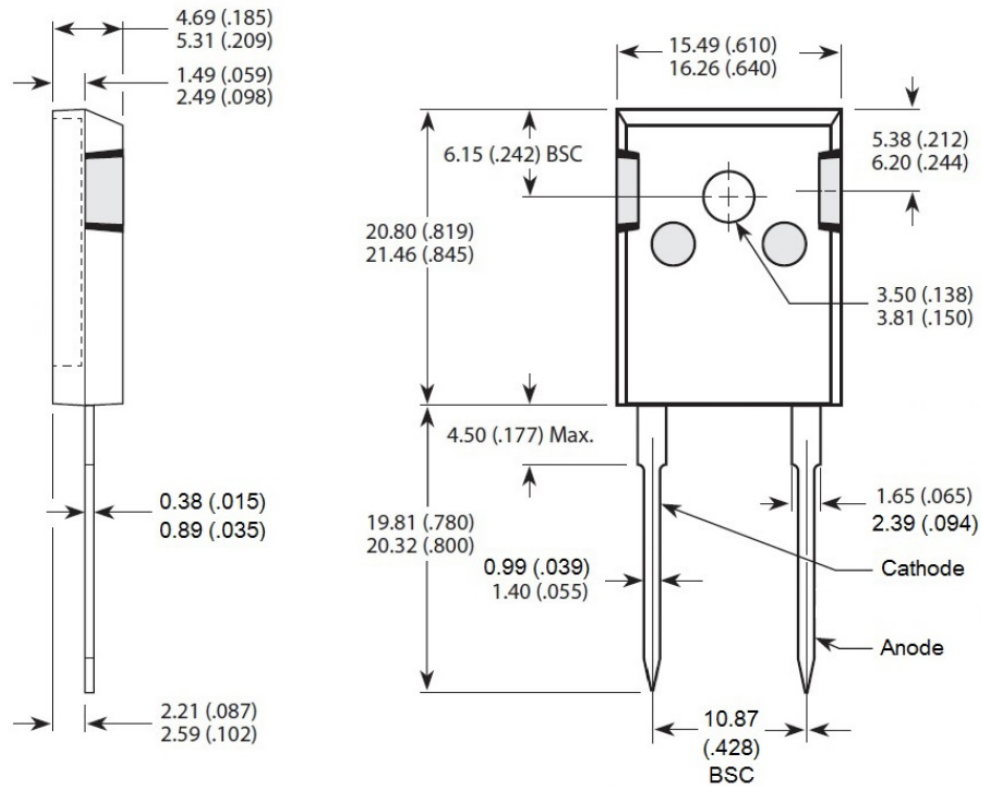
5 Package Specification

This section shows the package specification for the APT60DQ120BG device.

5.1 Package Outline Drawing

This section shows the TO-247 package drawing of the APT60DQ120BG device. Dimensions are in millimeters and (inches).

Figure 10 • Package Outline Drawing



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